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## **FDN5618P**

## 60V P-Channel Logic Level PowerTrench® MOSFET

## **General Description**

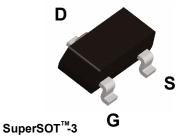
This 60V P-Channel MOSFET uses Fairchild's high voltage PowerTrench process. It has been optimized for power management applications.

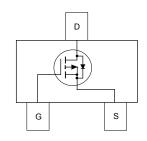
### **Applications**

- DC-DC converters
- Load switch
- · Power management

#### **Features**

- -1.25 A, -60 V.  $R_{DS(ON)} = 0.170 \Omega @ V_{GS} = -10 V$  $R_{DS(ON)} = 0.230 \Omega @ V_{GS} = -4.5 V$
- · Fast switching speed
- High performance trench technology for extremely low  $R_{\mbox{\scriptsize DS}(\mbox{\scriptsize ON})}$





## Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

| Symbol                            | Parameter  |           | Ratings     | Units |
|-----------------------------------|--|-----------|-------------|-------|
| V <sub>DSS</sub>                  | Drain-Source Voltage                             |           | <b>–</b> 60 | V     |
| V <sub>GSS</sub>                  | Gate-Source Voltage                              |           | ±20         | V     |
| I <sub>D</sub>                    | Drain Current - Continuous                       | (Note 1a) | -1.25       | А     |
|                                   | - Pulsed   |           | -10         |       |
|                                   | Maximum Power Dissipation                        | (Note 1a) | 0.5         | W     |
| $P_D$                             |  | (Note 1b) | 0.46        |       |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Junction Temperature Range |           | -55 to +150 | °C    |

## **Thermal Characteristics**

| $R_{\theta JA}$   | Thermal Resistance, Junction-to-Ambient | (Note 1a) | 250 | °C/W |
|-------------------|---|-----------|-----|------|
| R <sub>e,IC</sub> | Thermal Resistance, Junction-to-Case    | (Note 1)  | 75  | °C/W |

**Package Marking and Ordering Information** 

| Device Marking | Device   | Reel Size | Tape width | Quantity   |
|----------------|----------|-----------|------------|------------|
| 618            | FDN5618P | 7"        | 8mm        | 3000 units |

| Symbol                                      | Parameter   | Test Conditions  | Min        | Тур                     | Max                     | Units |
|---|---|--|------------|-------------------------|-------------------------|-------|
| Off Char                                    | acteristics                                       |  |            |                         |                         | I     |
| BV <sub>DSS</sub>                           | Drain-Source Breakdown Voltage                    | $V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$   | -60        |                         |                         | V     |
| <u>ΔBV<sub>DSS</sub></u><br>ΔT <sub>J</sub> | Breakdown Voltage Temperature Coefficient         | $I_D$ = -250 $\mu$ A,Referenced to 25°C  |            | -58                     |                         | mV/°C |
| I <sub>DSS</sub>                            | Zero Gate Voltage Drain Current                   | $V_{DS} = -48 \text{ V},  V_{GS} = 0 \text{ V}$  |            |                         | -1                      | μΑ    |
| I <sub>GSSF</sub>                           | Gate-Body Leakage, Forward                        | $V_{GS} = 20V$ , $V_{DS} = 0 V$  |            |                         | 100                     | nA    |
| I <sub>GSSR</sub>                           | Gate–Body Leakage, Reverse                        | $V_{GS} = -20 \text{ V}$ $V_{DS} = 0 \text{ V}$  |            |                         | -100                    | nA    |
| On Char                                     | racteristics (Note 2)                             |  |            |                         |                         |       |
| $V_{GS(th)}$                                | Gate Threshold Voltage                            | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$  | <b>–</b> 1 | -1.6                    | -3                      | V     |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$      | Gate Threshold Voltage<br>Temperature Coefficient | $I_D$ = -250 $\mu$ A,Referenced to 25°C  |            | 4                       |                         | mV/°C |
| R <sub>DS(on)</sub>                         | Static Drain–Source<br>On–Resistance              | $V_{GS} = -10 \text{ V},  I_D = -1.25 \text{ A}$<br>$V_{GS} = -4.5 \text{ V},  I_D = -1.0 \text{ A}$<br>$V_{GS} = -10 \text{ V}, I_D = -3 \text{ A} \text{ T}_J = 125^{\circ}\text{C}$ |            | 0.148<br>0.185<br>0.245 | 0.170<br>0.230<br>0.315 | Ω     |
| I <sub>D(on)</sub>                          | On-State Drain Current                            | $V_{GS} = -10 \text{ V}, \qquad V_{DS} = -5 \text{ V}$   | <b>-</b> 5 |                         |                         | Α     |
| <b>g</b> <sub>FS</sub>                      | Forward Transconductance                          | $V_{DS} = -5 \text{ V}, \qquad I_{D} = -1.25 \text{ A}$  |            | 4.3                     |                         | S     |
| Dynamic                                     | Characteristics                                   |  |            |                         |                         |       |
| C <sub>iss</sub>                            | Input Capacitance                                 | $V_{DS} = -30 \text{ V},  V_{GS} = 0 \text{ V},$   |            | 430                     |                         | pF    |
| Coss  | Output Capacitance                                | f = 1.0 MHz  |            | 52                      |                         | pF    |
| C <sub>rss</sub>                            | Reverse Transfer Capacitance                      |  |            | 19                      |                         | pF    |
| Switchin                                    | ng Characteristics (Note 2)                       |  |            |                         |                         |       |
| t <sub>d(on)</sub>                          | Turn-On Delay Time                                | $V_{DD} = -30 \text{ V}, \qquad I_{D} = -1 \text{ A},$   |            | 6.5                     | 13                      | ns    |
| t <sub>r</sub>                              | Turn-On Rise Time                                 | $V_{GS} = -10 \text{ V}, \qquad R_{GEN} = 6 \Omega$  |            | 8                       | 16                      | ns    |
| $t_{d(off)}$                                | Turn-Off Delay Time                               |  |            | 16.5                    | 30                      | ns    |
| t <sub>f</sub>                              | Turn-Off Fall Time                                |  |            | 4                       | 8                       | ns    |
| $Q_g$                                       | Total Gate Charge                                 | $V_{DS} = -30 \text{ V},  I_{D} = -1.25 \text{ A},$  |            | 8.6                     | 13.8                    | nC    |
| Q <sub>gs</sub>                             | Gate-Source Charge                                | V <sub>GS</sub> = -10 V  |            | 1.5                     |                         | nC    |
| $Q_{gd}$                                    | Gate-Drain Charge                                 |  |            | 1.3                     |                         | nC    |
| Drain-S                                     | ource Diode Characteristics                       | and Maximum Ratings  |            |                         |                         |       |
| Is  | Maximum Continuous Drain-Source                   |  |            |                         | -0.42                   | Α     |
| V <sub>SD</sub>                             | Drain–Source Diode Forward<br>Voltage             | $V_{GS} = 0 \text{ V},  I_S = -0.42  \text{(Note 2)}$  |            | -0.7                    | -1.2                    | V     |

## Notes:

<sup>1.</sup>  $R_{\theta,JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta,JC}$  is guaranteed by design while  $R_{\theta,CA}$  is determined by the user's board design.



a) 250°C/W when mounted on a 0.02 in² pad of 2 oz. copper.

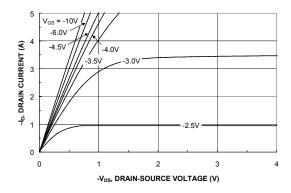


b) 270°C/W when mounted on a minimum pad.

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width  $\leq 300~\mu\text{s},~\text{Duty Cycle} \leq 2.0$ 

## **Typical Characteristics**



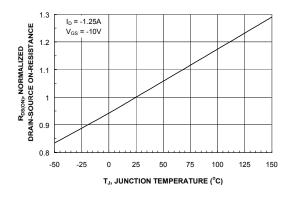
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Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.



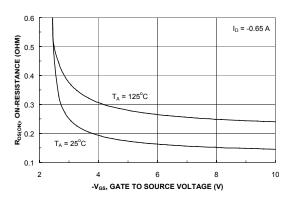
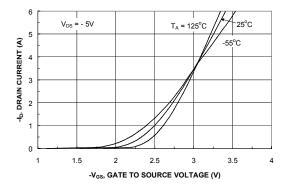


Figure 3. On-Resistance Variation withTemperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



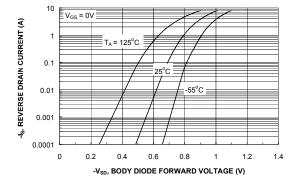
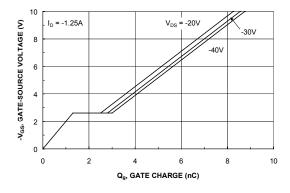


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## **Typical Characteristics**



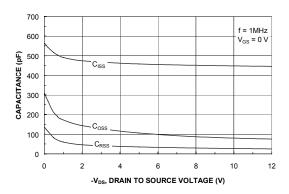
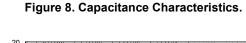
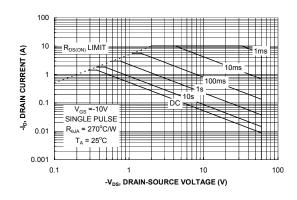


Figure 7. Gate Charge Characteristics.





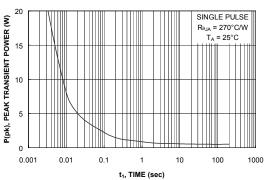


Figure 9. Maximum Safe Operating Area.



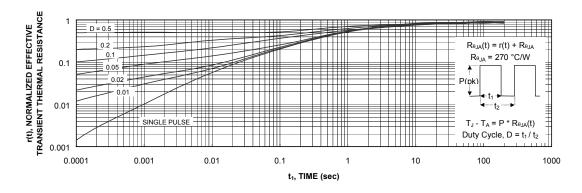


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

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